

P-Channel Enhancement Mode Power MOSFET

Description

The HM2P20Q uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = -200V, I_D = -2A$
 $R_{DS(ON)} < 1500m\Omega @ V_{GS} = -10V$ (Typ.=1250mR)

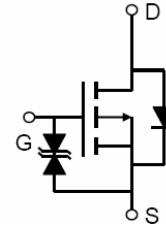
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

Application

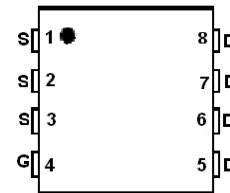
- Portable equipment and battery powered systems

100% UIS TESTED!

100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM2P20Q	HM2P20Q	DFN3X3-8L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-2	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	-1.4	A
Pulsed Drain Current	I_{DM}	-6	A
Maximum Power Dissipation	P_D	160	W
Derating factor		1.3	W/ $^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta jc}$	0.8	$^{\circ}\text{C}/\text{W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

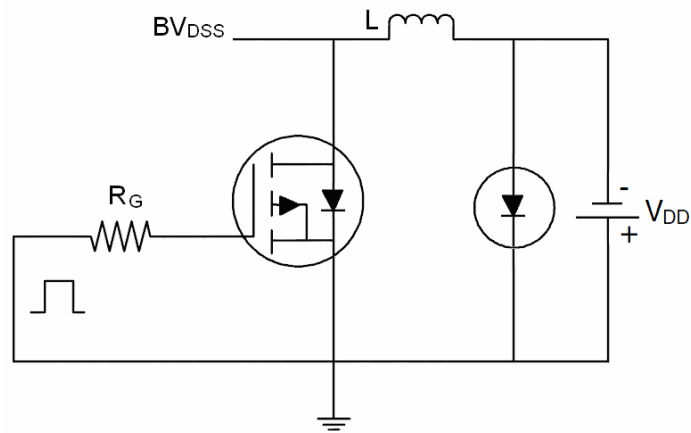
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-145	-155	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-145V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-4	-	-2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$	-	1250	1500	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-20A$	5	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-75V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	7650	-	PF
Output Capacitance	C_{oss}		-	148	-	PF
Reverse Transfer Capacitance	C_{rss}		-	131	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-75V, I_D=-20A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	17	-	nS
Turn-on Rise Time	t_r		-	80	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	nS
Turn-Off Fall Time	t_f		-	65	-	nS
Total Gate Charge	Q_g	$V_{DS}=-75V, I_D=-20A,$ $V_{GS}=-10V$	-	137	-	nC
Gate-Source Charge	Q_{gs}		-	25	-	nC
Gate-Drain Charge	Q_{gd}		-	28	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-11A$	-	-	-1.2	V
Diode Forward Current ^(Note 2)	I_S	-	-	-	-2	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = -11A$ $di/dt = 100A/\mu s$ ^(Note 3)	-	90	-	nS
Reverse Recovery Charge	Q_{rr}		-	105	-	nC

Notes:

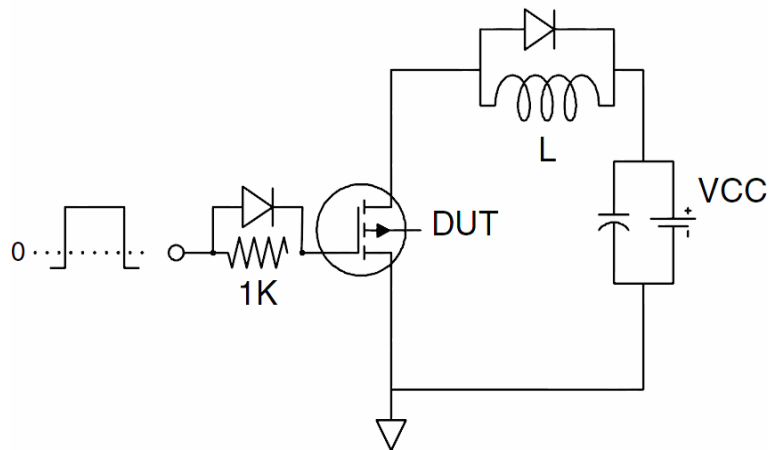
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=-75V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit

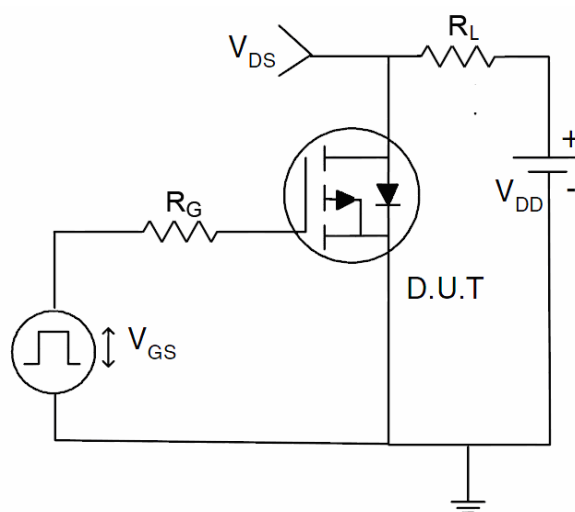
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

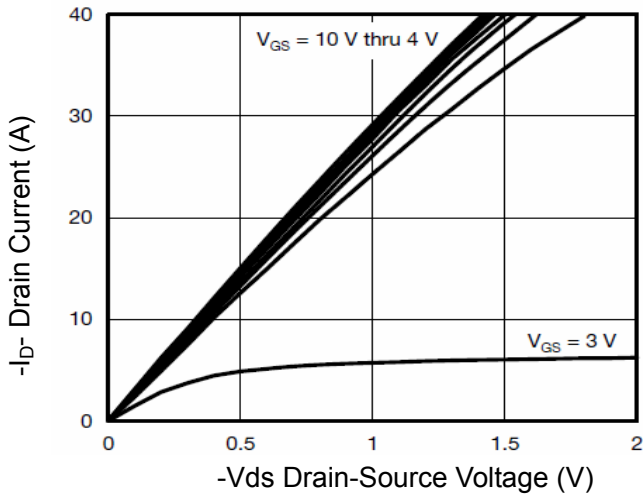


Figure 1 Output Characteristics

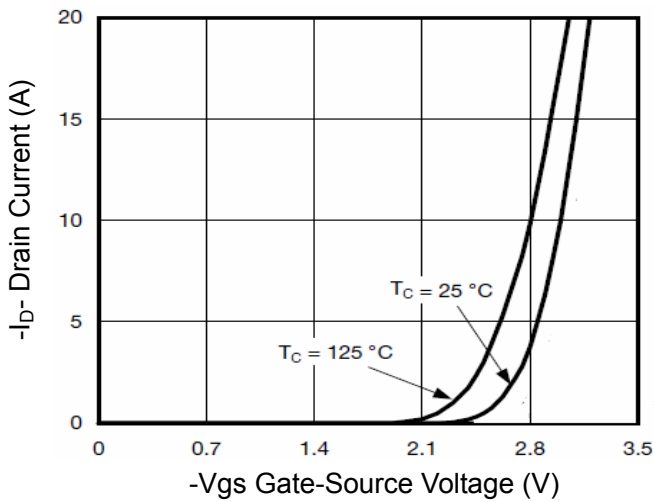


Figure 2 Transfer Characteristics

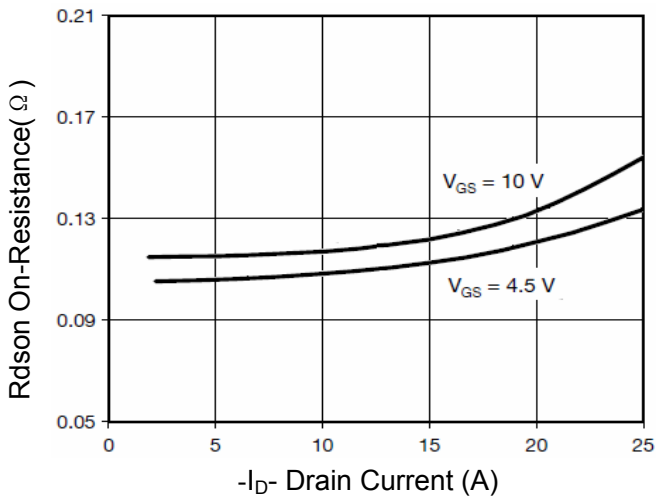


Figure 3 Rdson- Drain Current

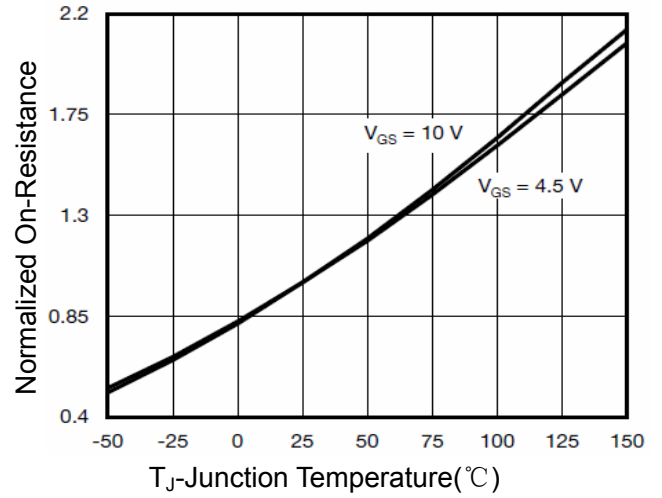


Figure 4 Rdson-Junction Temperature

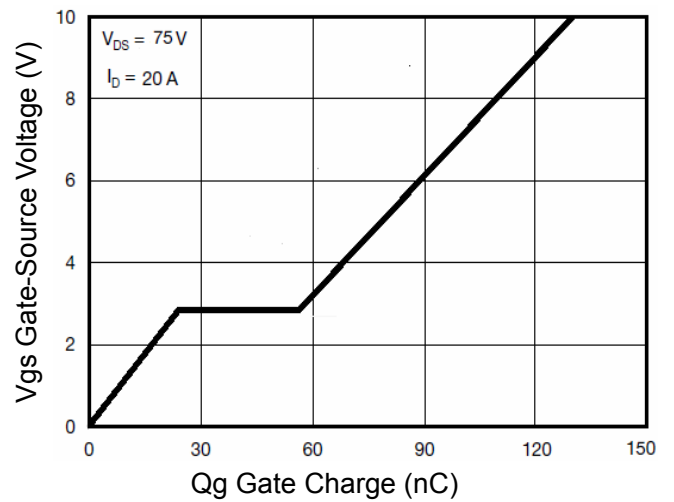


Figure 5 Gate Charge

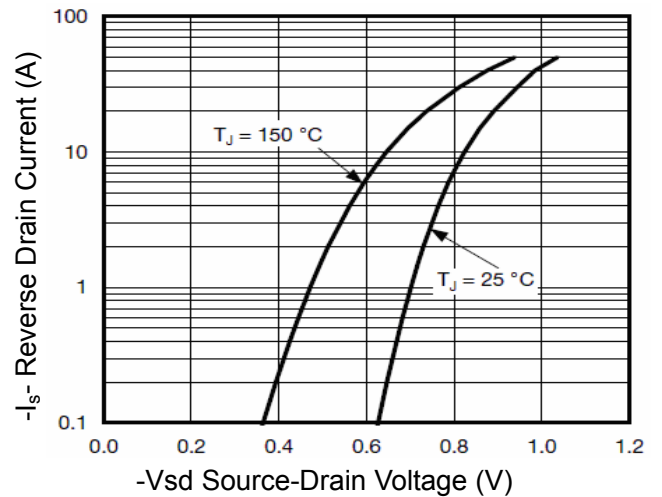


Figure 6 Source- Drain Diode Forward

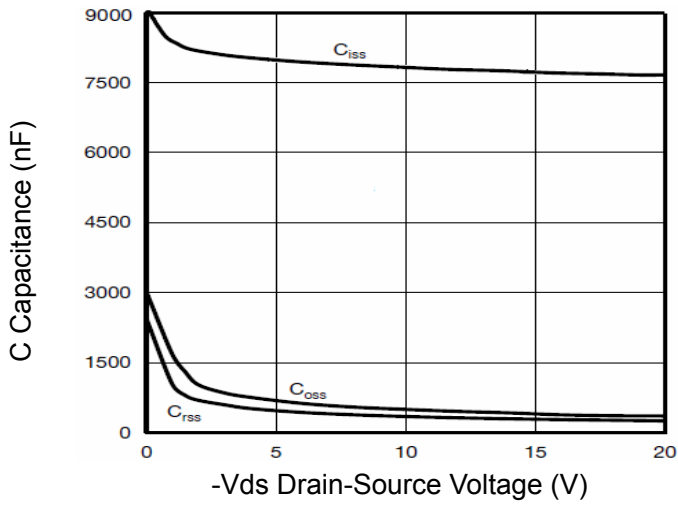


Figure 7 Capacitance vs Vds

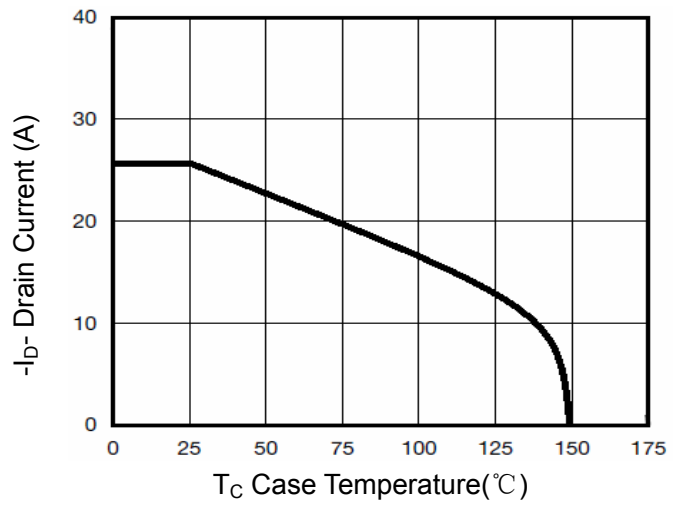


Figure 9 Drain Current vs Case Temperature

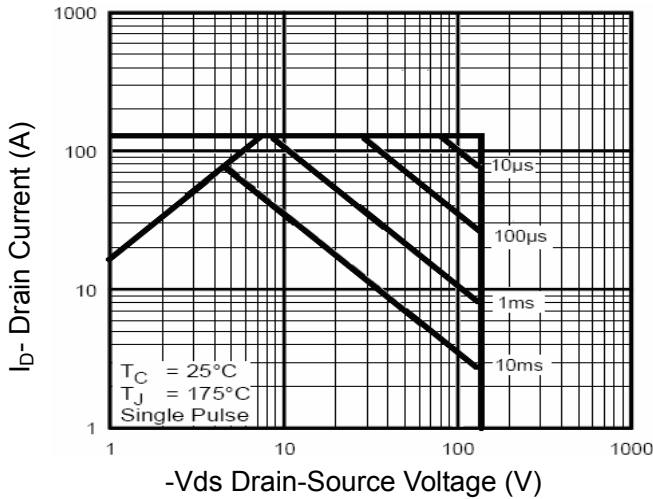


Figure 8 Safe Operation Area

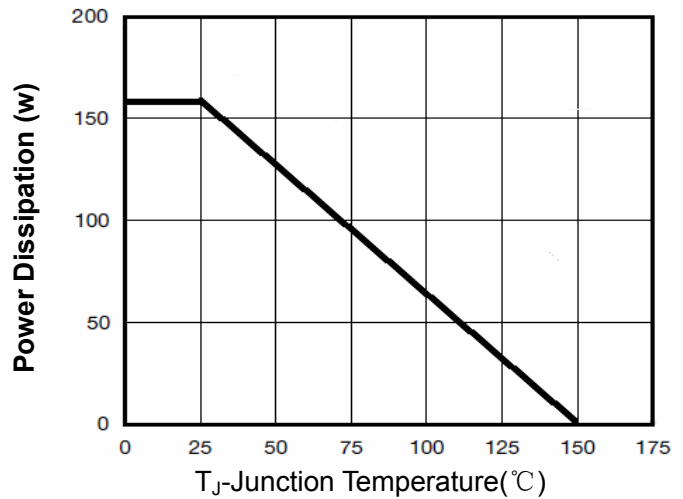


Figure 10 Power De-rating

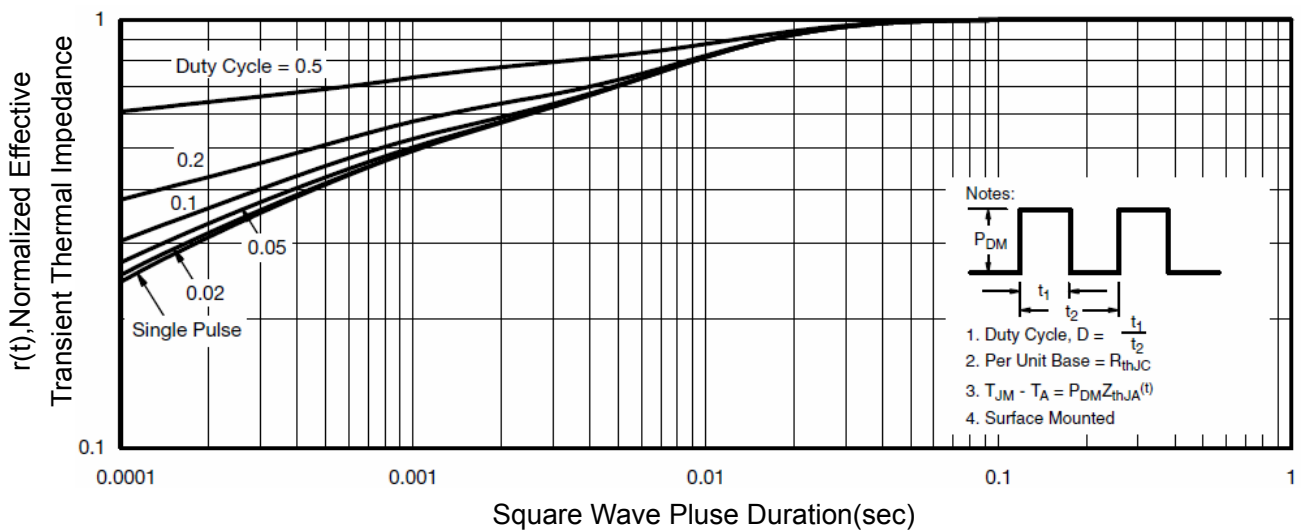
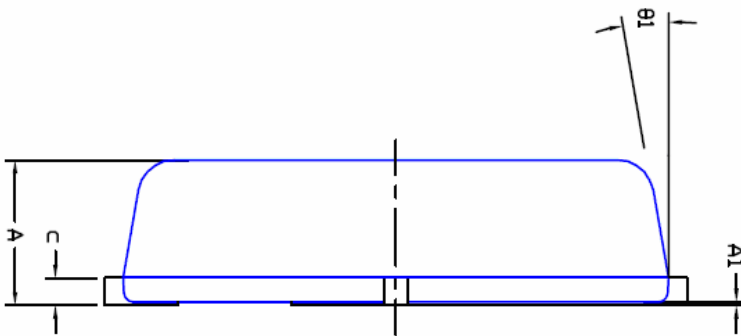
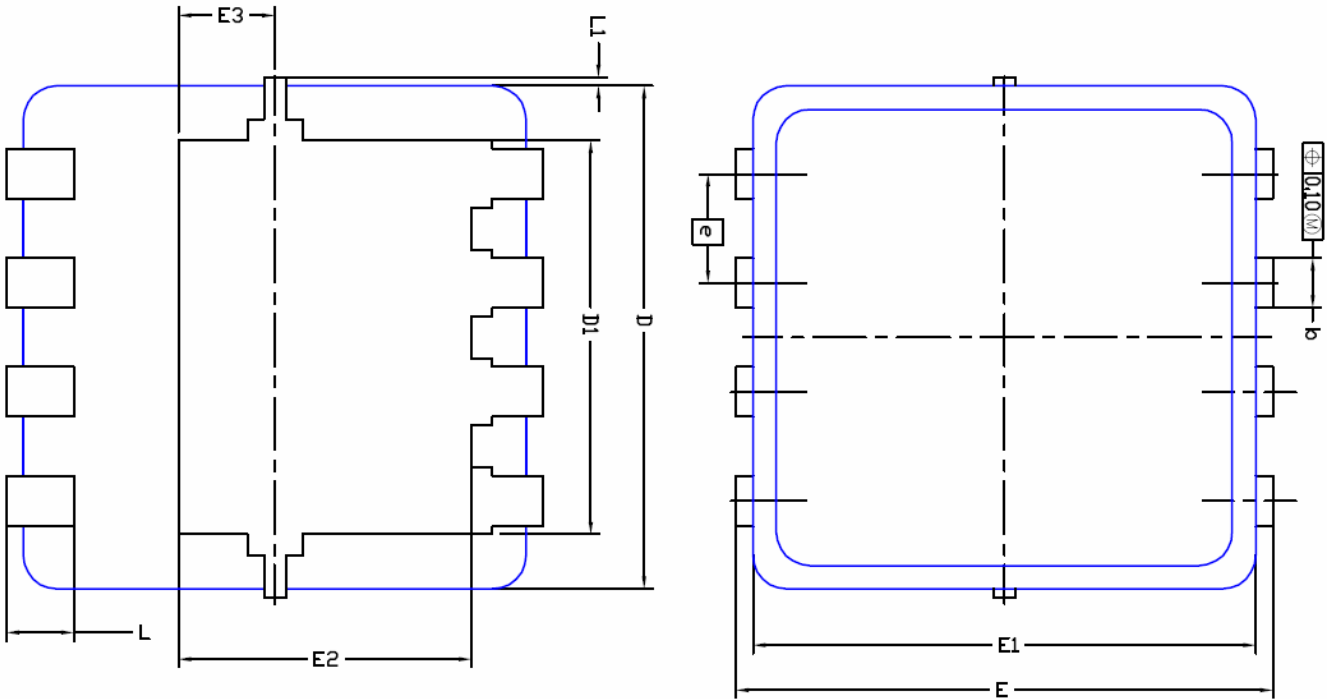


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0,700	0,80	0,900	0,0276	0,0315	0,0354
A1	0,00	---	0,05	0,000	---	0,002
b	0,24	0,30	0,35	0,009	0,012	0,014
c	0,10	0,152	0,25	0,004	0,006	0,010
D	3,00 BSC			0,118 BSC		
D1	2,35 BSC			0,093 BSC		
E	3,20 BSC			0,126 BSC		
E1	3,00 BSC			0,118 BSC		
E2	1,75 BSC			0,069 BSC		
E3	0,575 BSC			0,023 BSC		
e	0,65 BSC			0,026 BSC		
L	0,30	0,40	0,50	0,0118	0,0157	0,0197
L1	0	---	0,100	0	---	0,004
θ1	0°	10°	12°	0°	10°	12°